

BSS138AKA

60 V, single N-channel Trench MOSFET

29 April 2015

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	200	mA
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C		-	2.7	4.5	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BSS138AKA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23		

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
BSS138AKA	%JL

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	200	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	125	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	800	mA
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	300	mW
			[1]	-	360	mW
		T _{sp} = 25 °C		-	1060	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode			-	-	
Is	source current	T _{amb} = 25 °C	[1]	-	200	mA

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

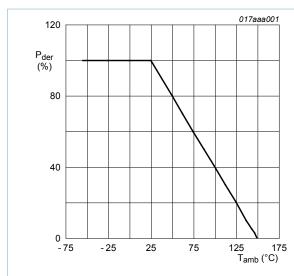


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25\%)}} \times \ \mathbf{100} \ \%$$

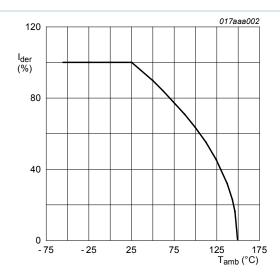


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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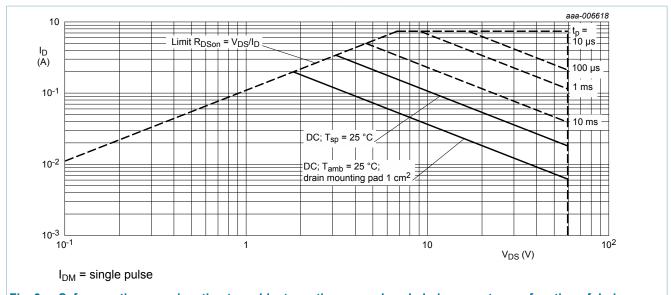


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uiy-a)	thermal resistance in		[1]	-	350	400	K/W
	from junction to ambient		[2]	-	300	340	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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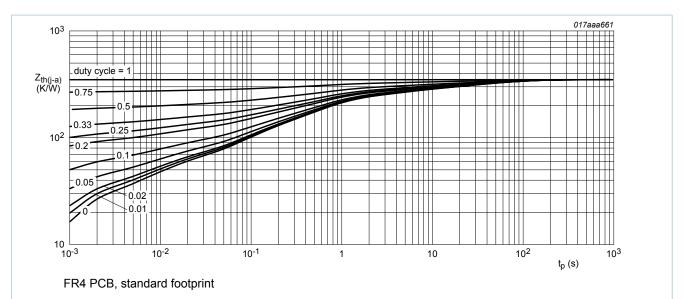


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

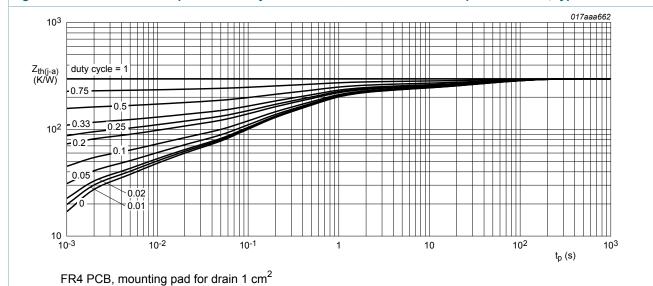


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \text{ A}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.8	1.2	1.5	V
I _{DSS} drain lea	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	3.5	μA
		V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-3.5	μA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-1	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μΑ
		V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 °C	-	-	-0.5	μΑ
200	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C	-	2.7	4.5	Ω
		V_{GS} = 10 V; I_D = 100 mA; pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_j = 150 \ ^{\circ}C$	-	5.5	9.2	Ω
		V_{GS} = 4.5 V; I_{D} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C	-	3	5.2	Ω
		V_{GS} = 2.5 V; I_{D} = 10 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{j}$ = 25 °C	-	4	13	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_{D} = 150 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{j} = 25 °C	320	-	-	mS
Dynamic cl	naracteristics		'			
Q _{G(tot)}	total gate charge	V _{DS} = 30 V; I _D = 150 mA; V _{GS} = 4.5 V;	-	0.39	0.51	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.1	-	nC
Q_{GD}	gate-drain charge		-	0.1	-	nC
C _{iss}	input capacitance	V _{DS} = 30 V; f = 1 MHz; V _{GS} = 0 V;	-	13	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.6	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 40 V; R_{L} = 250 Ω ; V_{GS} = 10 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	6	-	ns
$t_{d(off)}$	turn-off delay time		-	36	72	ns

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _f	fall time			-	22	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I_S = 115 mA; V_{GS} = 0 V; T_j = 25 °C		0.47	0.7	1.2	V

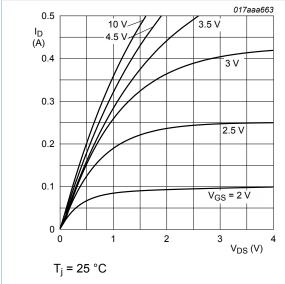


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

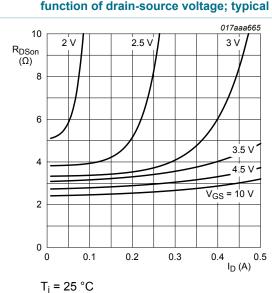


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

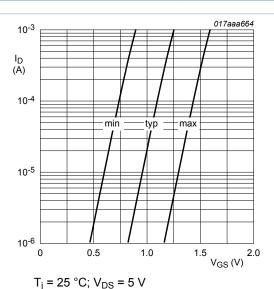


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

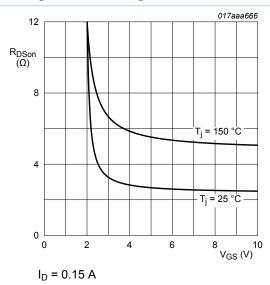


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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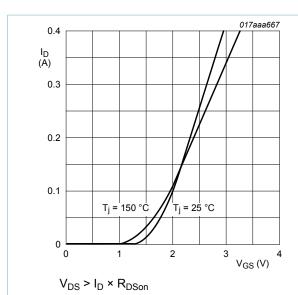


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

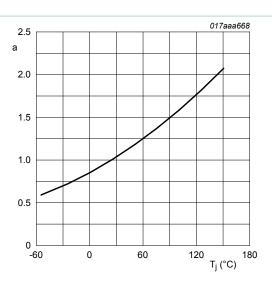


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

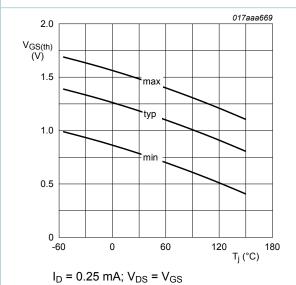
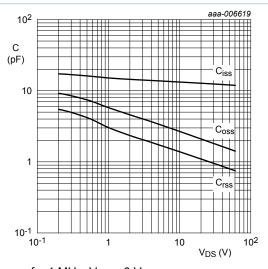


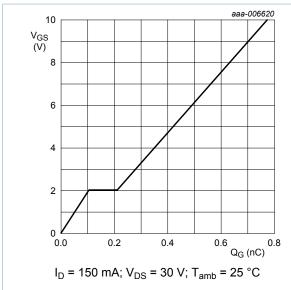
Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V_{GS}(pl)

V_{GS}(pl)

V_{GS}(th)

V_{GS}

Q_{GS1}
Q_{GS2}
Q_{GG}(tot)

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Fig. 15. Gate charge waveform definitions

Fig. 14. Gate-source voltage as a function of gate charge; typical values

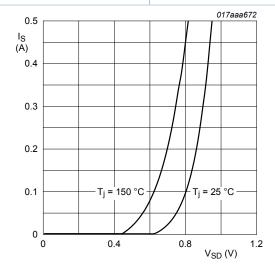
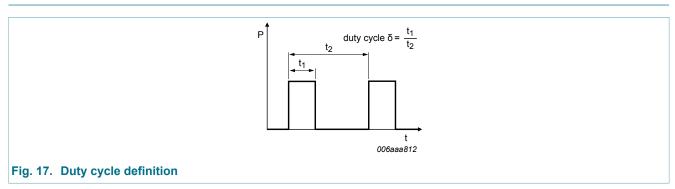


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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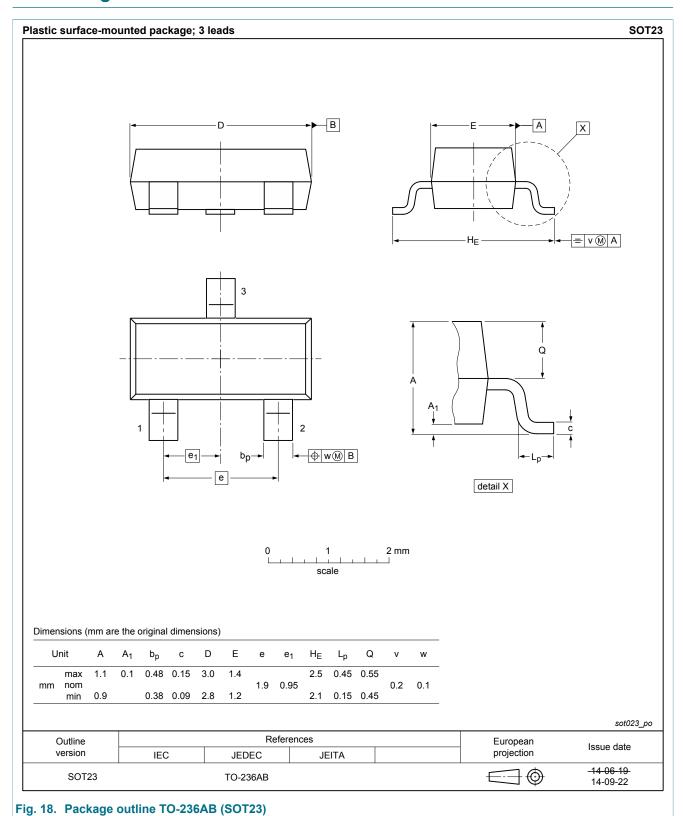
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11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

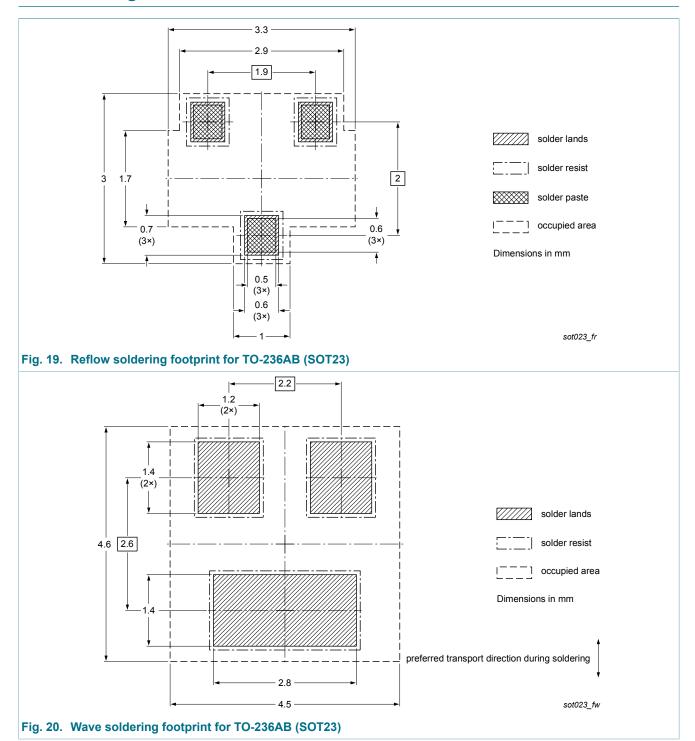
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
BSS138AKA v.3	20150429	Product data sheet	-	BSS138AKA v.2			
Modifications:	Figure 14: x-axis sc	Figure 14: x-axis scale corrected					
BSS138AKA v.2	20141103	Product data sheet	-	BSS138AKA v.1			
BSS138AKA v.1	20130206	Product data sheet	-	-			

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15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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